

N-channel TrenchMOS logic level FET 7 April 2014

Product data sheet

## 1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

## 2. Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

## 3. Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

## 4. Quick reference data

Table 1. Qu	ick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	55	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	[1]	-	-	62	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	115	W
Static charac	teristics						
R <sub>DSon</sub>		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C		-	11	13.6	mΩ
	resistance	$V_{GS}$ = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C		-	-	16.6	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11; Fig. 12		-	13	15	mΩ
Dynamic cha	racteristics	·					
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 44 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>		-	20	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Avalanche rug	gedness	·				
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 62 A; $V_{sup} \le 55$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	211	mJ

[1] Current is limited by power dissipation chip rating.

## 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G
mb	D	mounting base; connected to drain		mbb076 S
			DPAK (SOT428)	

## 6. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
BUK9215-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

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#### **Limiting values** 7.

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

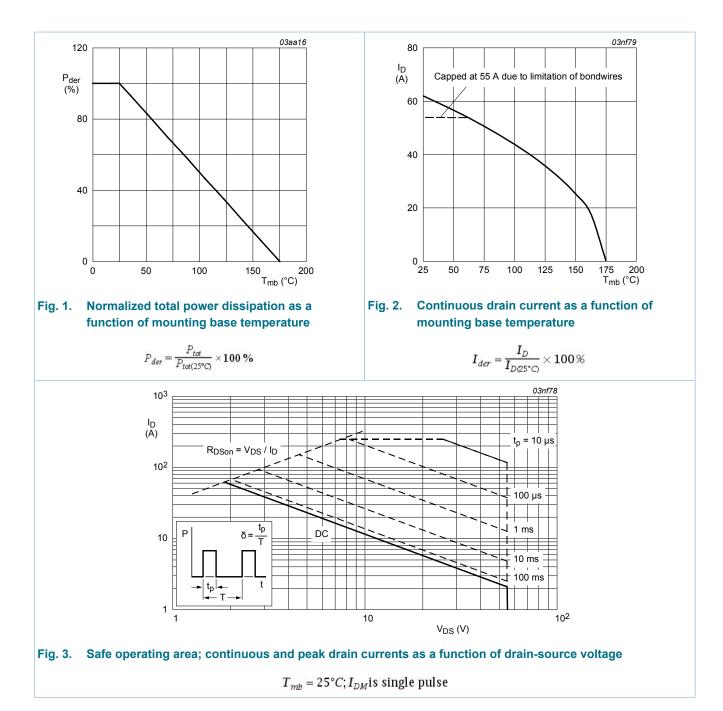
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	55	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ		-	55	V
V <sub>GS</sub>	gate-source voltage			-15	15	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	115	W
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2; Fig. 3</u>	[1]	-	62	А
			[2]	-	55	А
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2</u>	[1]	-	44	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \ \mu s$ ; Fig. 3		-	248	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
ls	source current	T <sub>mb</sub> = 25 °C	[2]	-	55	А
			[1]	-	62	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	248	А
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 62 A; $V_{sup} \le 55$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	211	mJ

Current is limited by power dissipation chip rating.
Continious current is limited by bond wires.

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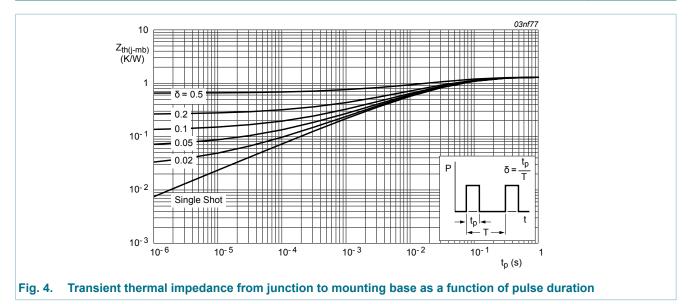
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## 8. Thermal characteristics

Table 5. Th	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4	-	-	1.3	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		-	71.4	-	K/W



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## 9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	11				
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	55	-	-	V
	breakdown voltage	$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	50	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; Fig. 10	-	-	2.3	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; Fig. 10	0.5	-	-	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; Fig. 10	1	1.5	2	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 55 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.05	10	μA
	gate leakage current	V <sub>DS</sub> = 55 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		$V_{GS}$ = -10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	11	13.6	mΩ
	resistance	$V_{GS}$ = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	-	16.6	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 11; Fig. 12	-	-	30	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11; Fig. 12	-	13	15	mΩ
Dynamic ch	naracteristics					_
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 25 A; $V_{DS}$ = 44 V; $V_{GS}$ = 5 V;	-	48	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	6	-	nC
Q <sub>GD</sub>	gate-drain charge		-	20	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	2190	2916	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 13</u>	-	380	450	pF
C <sub>rss</sub>	reverse transfer capacitance		-	250	344	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; R <sub>L</sub> = 1.2 Ω; V <sub>GS</sub> = 5 V;	-	19	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 10 Ω; T <sub>j</sub> = 25 °C	-	161	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	138	-	ns
t <sub>f</sub>	fall time		-	165	-	ns
L <sub>D</sub>	internal drain inductance	measured from drain to centre of die	-	2.5	-	nH

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
L <sub>S</sub>	internal source inductance	measured from source lead to source bond pad	-	7.5	-	nH
Source-drain	diode	·				,
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 20 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 14</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 20 A; dI <sub>S</sub> /dt = -100 A/μs;	-	51	-	ns
Q <sub>r</sub>	recovered charge	V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 30 V; T <sub>j</sub> = 25 °C	-	102	-	nC

19 R<sub>DSon</sub>

κ<sub>DSol</sub>. (mΩ) 18

17

16

15

14

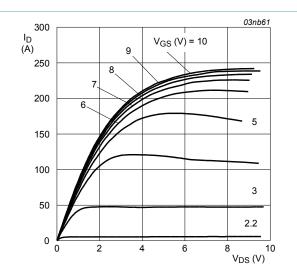
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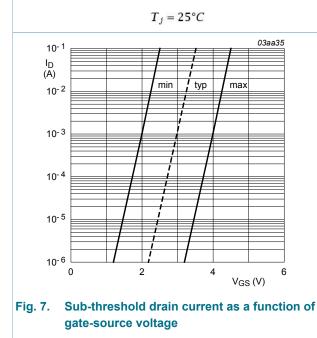
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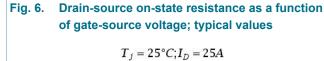
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 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$ 



9

12

V<sub>GS</sub> (V)

15

6

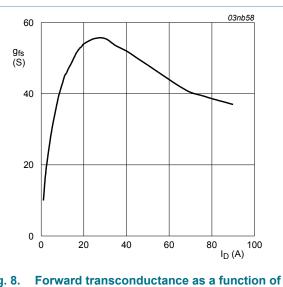
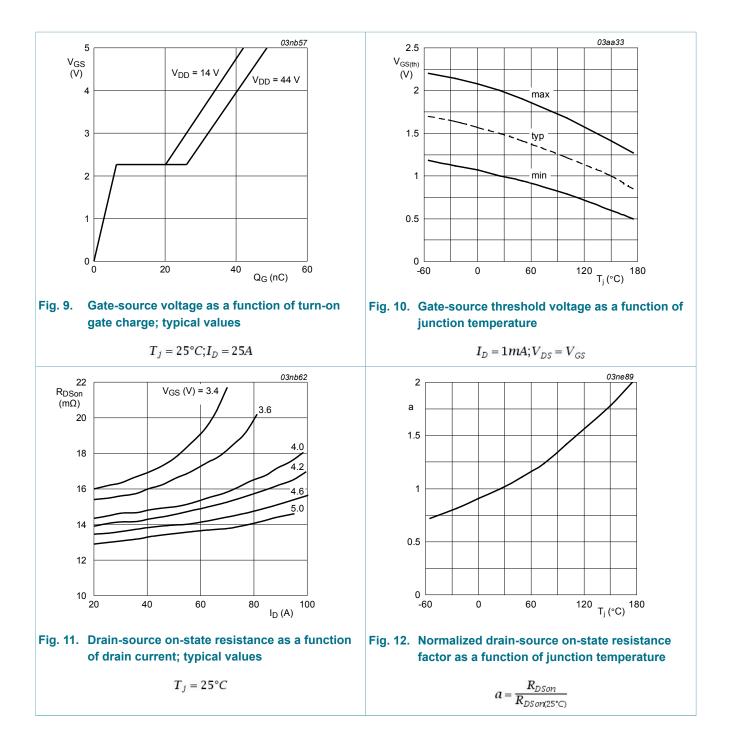


Fig. 8. drain current; typical values

 $T_j = 25^{\circ}C; V_{DS} = 25V$ 

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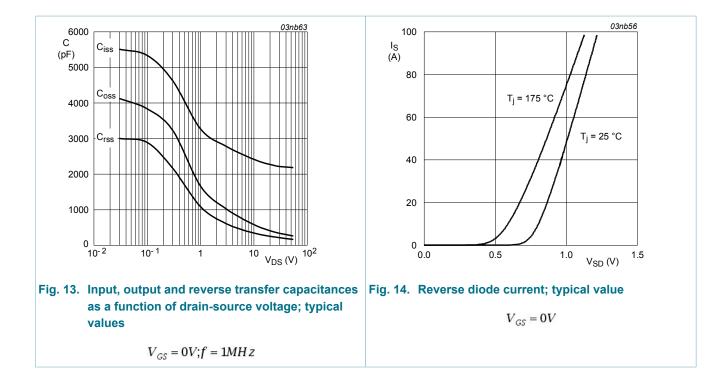


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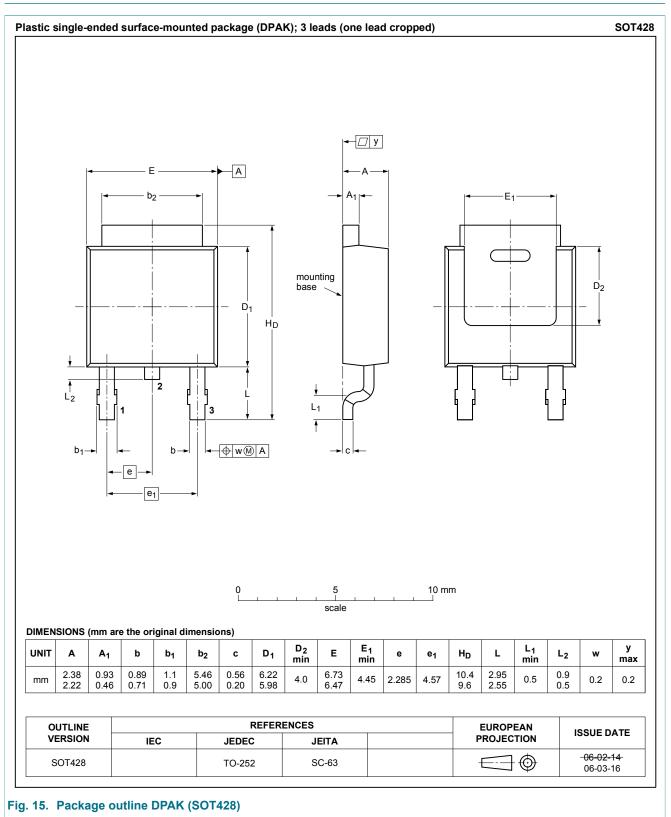
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## 10. Package outline



BUK9215-55A

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## 11. Legal information

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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